ON Semiconductor®

FDS4141-F085

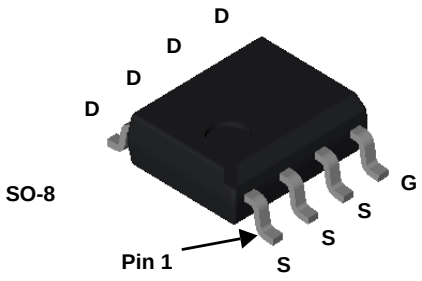
P-Channel PowerTrench® MOSFET
-40V, -10.8A, 19.0mΩ

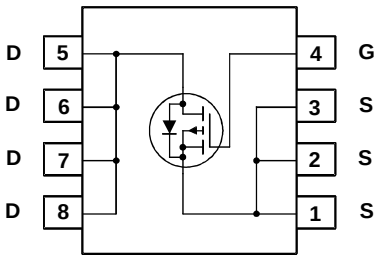
Features

- Typ $r_{DS(on)}$ = 10.5mΩ at V_{GS} = -10V, I_D = -10.5A
- Typ $r_{DS(on)}$ = 14.8mΩ at V_{GS} = -4.5V, I_D = -8.4A
- Typ $Q_{g(TOT)}$ = 35nC at V_{GS} = -10V
- High performance trench technology for extremely low $r_{DS(on)}$
- RoHS Compliant
- Qualified to AEC Q101

Applications

- Control switch in synchronous & non-synchronous buck
- Load switch
- Inverter





September-2017,Rev. 1

Publication Order Number:
FDS4141-F085/D

MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	-40	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current Continuous (V_{GS} = 10V)	-10.8	A
	Pulsed	-36	
E_{AS}	Single Pulse Avalanche Energy	229	mJ
P_D	Power Dissipation	1.6	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	30	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient SO-8, 1in^2 copper pad area	81	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS4141	FDS4141-F085	SO-8	13”	12mm	2500 units

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -32V,	-	-	-1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V,	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250μA	-1.0	-1.7	-3.0	V
$r_{DS(on)}$	Drain to Source On Resistance	I_D = -10.5A, V_{GS} = -10V	-	10.5	13.0	mΩ
		I_D = -8.4A, V_{GS} = -4.5V	-	14.8	19.0	
		I_D = -10.5A, V_{GS} = -10V, T_J = 125°C	-	15.3	19.0	
g_{FS}	Forward Transconductance	I_D = -10.5A, V_{DD} = -5V		34		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -20V, V_{GS} = 0V, f = 1MHz	-	2005	-	pF
C_{oss}	Output Capacitance		-	355	-	pF
C_{rss}	Reverse Transfer Capacitance		-	190	-	pF
R_g	Gate Resistance	f = 1MHz	-	5.0	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at -10V	V_{GS} = 0 to -10V; V_{DD} = -20V, I_D = -10.5A	-	35	45	nC
$Q_{g(-5)}$	Total Gate Charge at -5V	V_{GS} = 0 to -5V; V_{DD} = -20V, I_D = -10.5A	-	18.6	24.2	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = -20V, I_D = -10.5A	-	5.2	-	nC
Q_{gd}	Gate to Drain “Miller“ Charge	V_{DD} = -20V, I_D = -10.5A	-	6.6	-	nC

Electrical Characteristics $T_A = 25^oC$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Switching Characteristics						
t_{on}	Turn-On Time	V_{DD} = -20V, I_D = -10.5A V_{GS} = -10V, R_{GEN} = 6Ω	-	-	25	ns
$t_{d(on)}$	Turn-On Delay Time		-	9.7	-	ns
t_r	Rise Time		-	4.4	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	41	-	ns
t_f	Fall Time		-	11.6	-	ns
t_{off}	Turn-Off Time		-	-	84	ns
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	I_{SD} = -10.5A	-	-0.8	-1.3	V
		I_{SD} = -2.1A	-	-0.7	-1.2	
t_{rr}	Reverse Recovery Time	I_F = -10.5A, d_{SD}/dt = 100A/μs	-	26	34	ns
Q_{rr}	Reverse Recovery Charge		-	13.4	17.4	nC

Notes:

1: Starting $T_J = 25^oC$, L = 6.2mH, I_{AS} = -8.6A

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/
All ON Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

Typical Characteristics

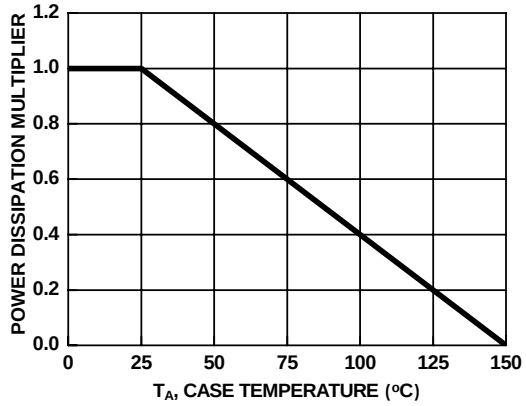


Figure 1. Normalized Power Dissipation vs Ambient Temperature

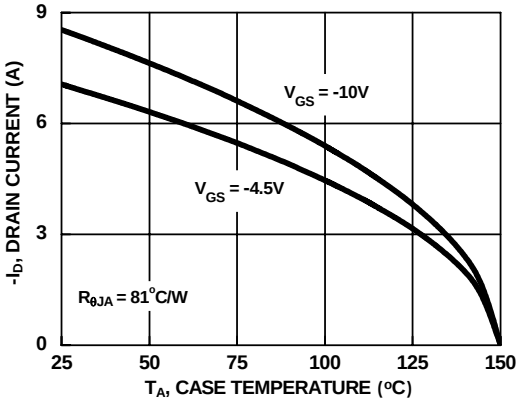


Figure 2. Maximum Continuous Drain Current vs Ambient Temperature

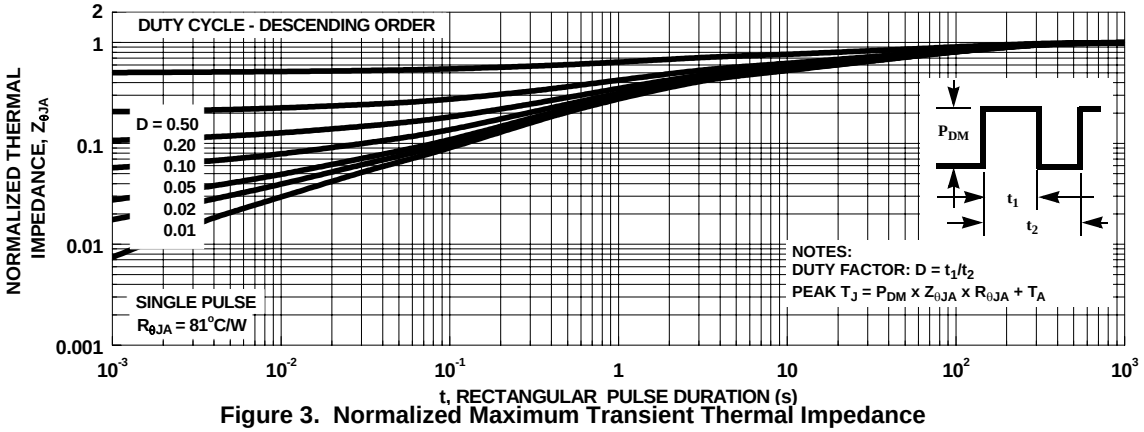


Figure 3. Normalized Maximum Transient Thermal Impedance

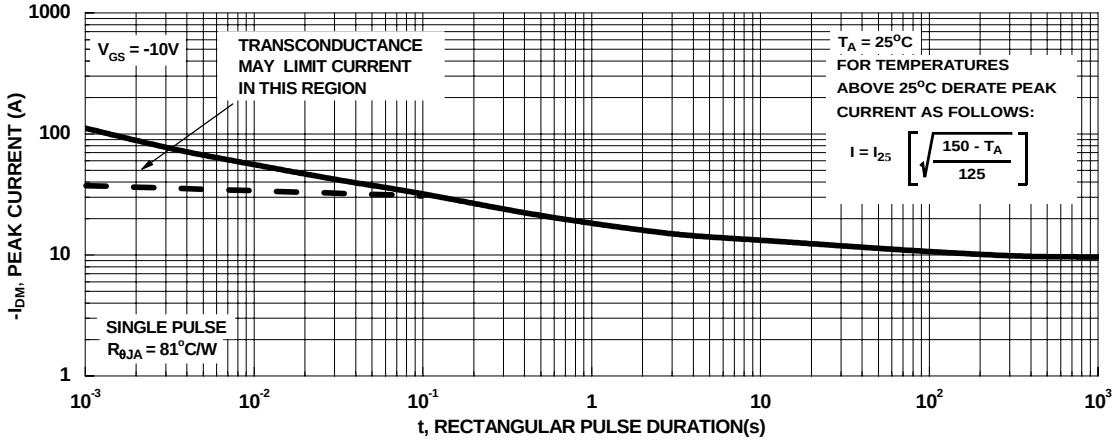


Figure 4. Peak Current Capability

Typical Characteristics

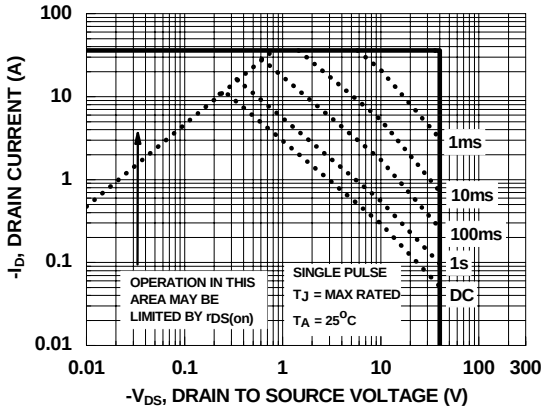
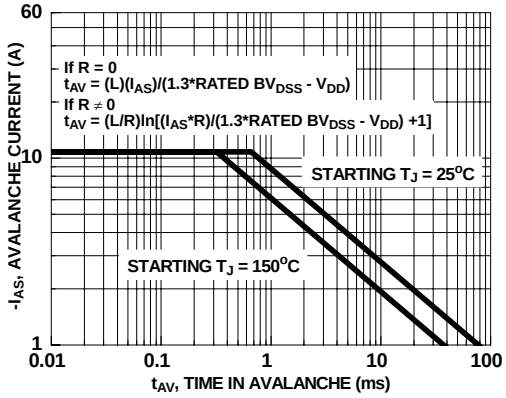


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

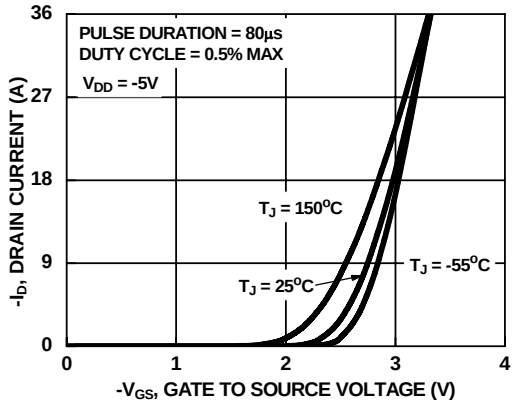


Figure 7. Transfer Characteristics

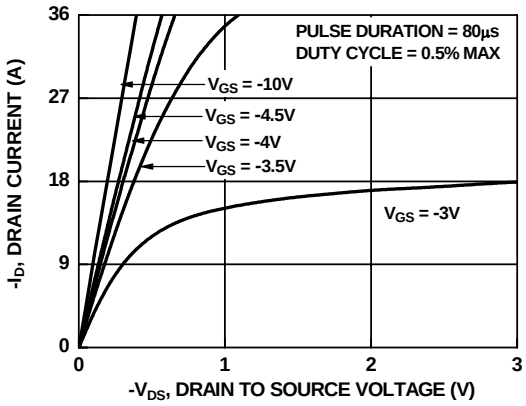


Figure 8. Saturation Characteristics

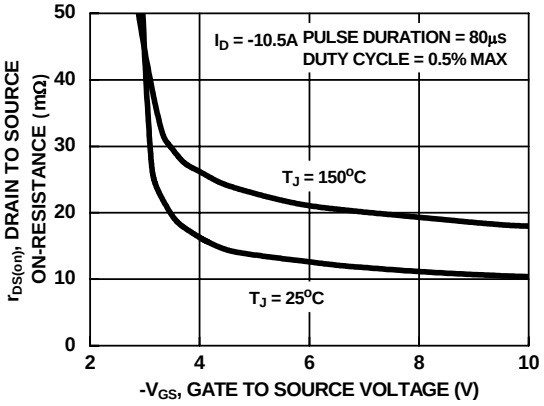


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

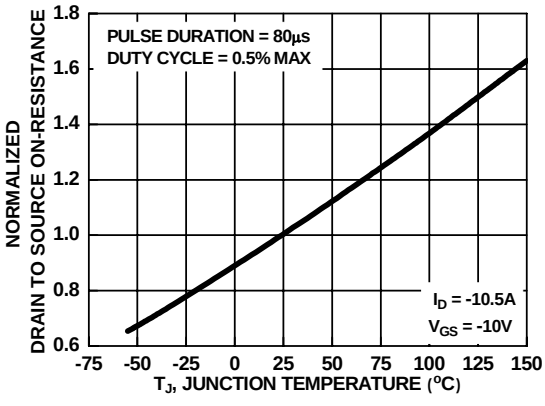


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

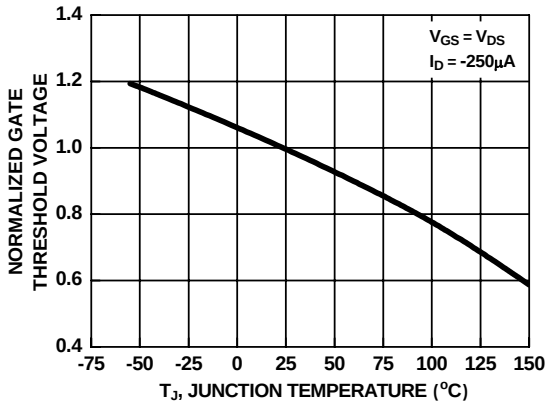


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

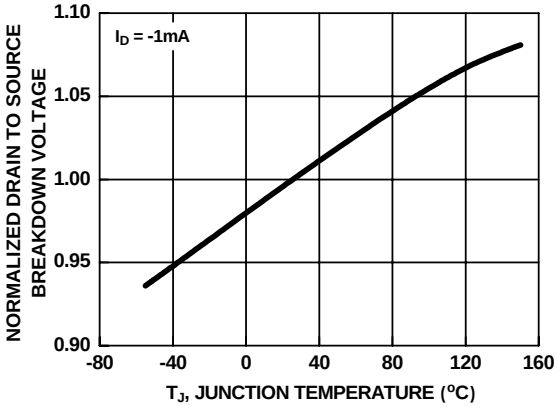


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

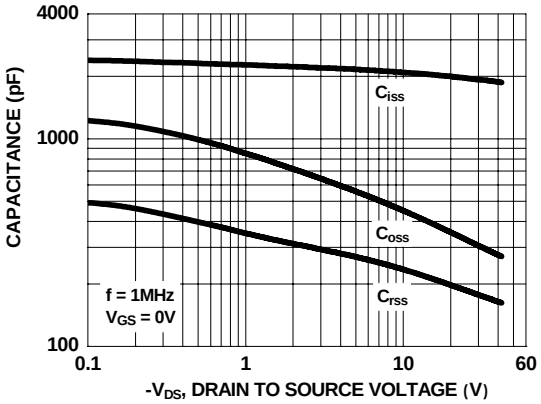


Figure 13. Capacitance vs Drain to Source Voltage

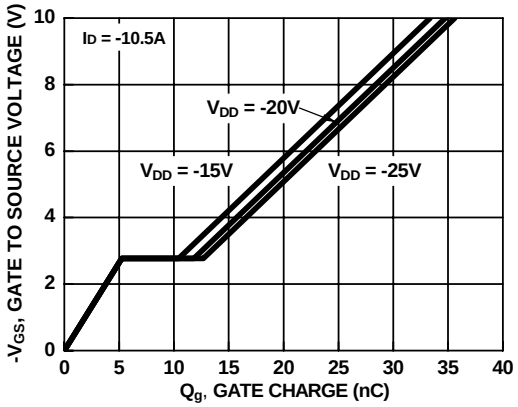


Figure 14. Gate Charge vs Gate to Source Voltage

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